

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	28	((tft or (thin adj film adj transistor)) with (thickness) with channel with gate with threshold with voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 00:53
L2	16	((tft or (thin adj film adj transistor)) with ((thickness) near10 channel near10 gate near10 threshold near10 voltage))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 00:54
L3	15	((tft or (thin adj film adj transistor)) with ((thickness) near10 channel near10 gate near10 (threshold near voltage)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 00:54
L4	9	((tft or (thin adj film adj transistor)) with ((thickness) near10 channel near10 gate near (threshold near voltage)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 00:54
L5	1	((tft or (thin adj film adj transistor)) with ((thickness) near5 channel near5 gate near (threshold near voltage)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 00:55
L6	1	((tft or (thin adj film adj transistor)) same ((thickness) near5 channel near5 gate near (threshold near voltage)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 00:55
L7	9	((tft or (thin adj film adj transistor)) same ((thickness) near10 channel near10 gate near (threshold near voltage)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 00:55
L8	1	((tft or (thin adj film adj transistor)) same ((thickness) near channel near10 gate near (threshold near voltage)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 00:55
L9	2	((tft or (thin adj film adj transistor)) same ((thickness) near2 channel near10 gate near (threshold near voltage)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 00:56

L10	19	((thickness) near2 channel near10 gate near (threshold near voltage))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 00:56
L11	1	((thickness) near2 channel near10 gate near (threshold near voltage)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 00:56
L12	19	((thickness) near2 channel near10 gate near (threshold near voltage))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 00:57
L13	2	((thickness) near2 channel near10 gate near (threshold near voltage)) and (thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 01:00
L14	12279	(thickness near3 channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 01:00
L15	216	(thickness near3 channel) near10 (threshold adj voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 01:00
L16	2	(thickness near3 channel) near10 (threshold adj voltage) near10 (thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 01:01
L17	3	(thickness near3 channel) with (threshold adj voltage) with (thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 01:01
L18	4	(thickness near3 channel) same (threshold adj voltage) with (thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 01:01
L19	12	(thickness near3 channel) same (threshold adj voltage) same (thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 01:02

L20	2	((thickness near3 channel) same (threshold adj voltage) same (thin adj film adj transistor)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 01:02
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